



DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

Device	BV _{DSS}	Rds(on) max	ID MAX TA = +25°C
N-Channel	20V	40mΩ @ V _{GS} = 4.5V	4.7A
IN-CHAINE	200	65mΩ @ V _{GS} = 2.5V	3.7A

Description

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Load Switch
- Power Management Functions
- Portable Power Adaptors

Features

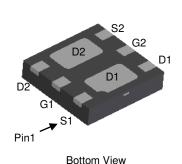
- Low On-Resistance
- Low Input Capacitance
- Low Profile, 0.6mm Max Height
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

https://www.diodes.com/quality/product-definitions/

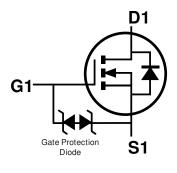
Mechanical Data

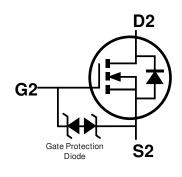
- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (4)
- Terminal Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)





U-DFN2020-6 (Type B)





Q1 N-CHANNEL

Q2 N-CHANNEL

Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2041UFDB-7	U-DFN2020-6 (Type B)	3,000/Tape & Reel
DMN2041UFDB-13	U-DFN2020-6 (Type B)	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information

Site 1

U-DFN2020-6 (Type B)



D7 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020)M = Month (ex: 9 = September)

Date Code Kev

Date Code Rey												
Year	2014		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	В		Н	I	J	K	L	М	N	0	Р	R
	1	1	1	1	1			1	1	1	I.	1
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Site 2



D7 = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 0 = 2020)

W = Week (ex: a = week 27; z represents week 52 and 53) X = Internal Code (ex: U = Monday)

Date Code Key

Year	2014	 2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	4	 0	1	2	3	4	5	6	7	8	9

Week	1-26	27-52	53
Code	A-Z	a-z	Z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	T	U	V	W	X	Υ	Z



Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage			Vgss	±12	V
Continuous Drain Current (Note 5) Voc. 45V	Steady State	T _A = +25°C T _A = +70°C	lD	4.7 3.8	А
Continuous Drain Current (Note 5) VGS = 4.5V	t < 5s	T _A = +25°C T _A = +70°C	I _D	6.1 4.9	А
Maximum Continuous Body Diode Forward Curre	Is	2	Α		
Pulsed Drain Current (10µs Pulse, Duty Cycle =	1%)		I _{DM}	20	Α

Thermal Characteristics

Characteristic		Symbol	Value	Unit	
Total Dawer Dissination (Note 5)	Steady State	D-	1.4	W	
Total Power Dissipation (Note 5)	t < 5s	PD	2.2	VV	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Б	92		
Thermal nesistance, sunction to Ambient (Note 5)	t < 5s	R⊕JA	55	°C/W	
Thermal Resistance, Junction to Case (Note 5)	Rejc	30			
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C	

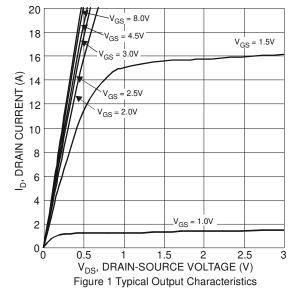
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

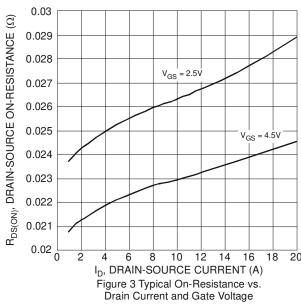
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current T _J = +25°C	IDSS	_	_	1.0	μΑ	V _{DS} = 20V, V _{GS} = 0V
Gate-Source Leakage	Igss	-	_	±10	μΑ	$V_{GS} = \pm 8V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(TH)}	0.35	_	1.4	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	D	_	23	40	mΩ	VGS = 4.5V, ID = 4.2A
Static Drain-Source On-Resistance	RDS(ON)	_	26	65	11122	VGS = 2.5V, ID = 3.3A
Diode Forward Voltage	V _{SD}	-	0.75	1.2	V	VGS = 0V, IS = 4.4A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C _{iss}	_	713	_	pF	
Output Capacitance	Coss	_	80	_	pF	V _{DS} = 10V, V _{GS} = 0V, f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	_	68	_	pF	1 = 1.000112
Gate Resistance	Rg	_	15	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge (V _{GS} = 4.5V)			8	_	nC	
Total Gate Charge (V _{GS} = 8V)	Qg		15	_	nC	10/ 10/ 1 5.54
Gate-Source Charge	Qgs	-	1.0	_	nC	$V_{DS} = 10V, I_{D} = 5.5A$
Gate-Drain Charge	Qgd	-	1.1	_	nC	
Turn-On Delay Time	tD(ON)	_	3.6	_	ns	
Turn-On Rise Time	t _R	1	15.9	_	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$
Turn-Off Delay Time	t _{D(OFF)}	1	16.0	1	ns	$R_L = 2.3\Omega$, $R_G = 1\Omega$
Turn-Off Fall Time	tr	_	2.6	_	ns	
Body Diode Reverse Recovery Time	trr	-	6.6	_	ns	$I_S = 4.4A$, $dI/dt = 100A/\mu s$
Body Diode Reverse Recovery Charge	Q _{RR}	_	1.2	_	nC	I _S = 4.4A, dI/dt = 100A/µs

5. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided. Notes:

Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.







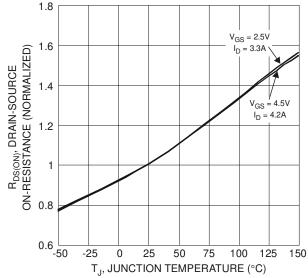
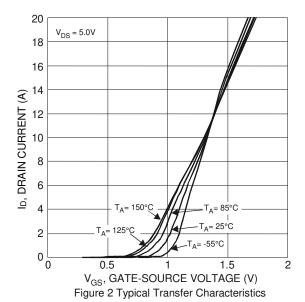


Figure 5 On-Resistance Variation with Temperature



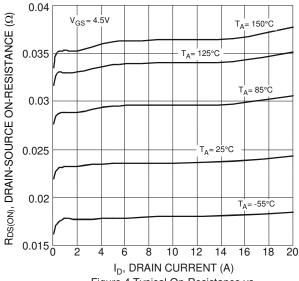


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

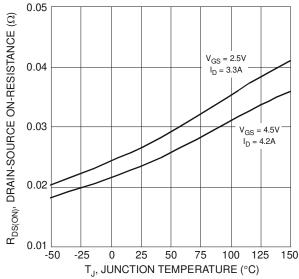


Figure 6 On-Resistance Variation with Temperature



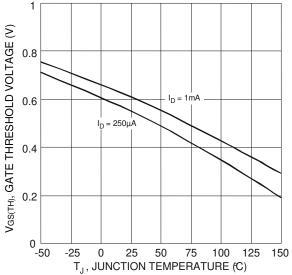
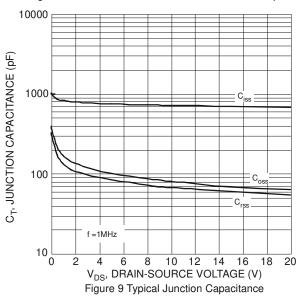
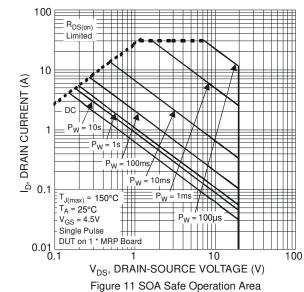
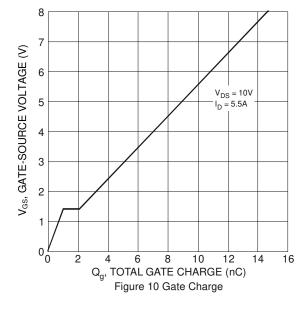


Figure 7 Gate Threshold Variation vs. Junction Temperature





20 18 16 Is, SOURCE CURRENT (A) 14 12 10 8 6 2 0 0 0.6 0.9 1.2 1.5 V_{SD}, SOURCE-DRAIN VOLTAGE (V) Figure 8 Diode Forward Voltage vs. Current





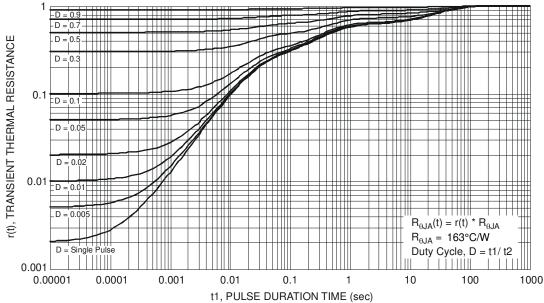


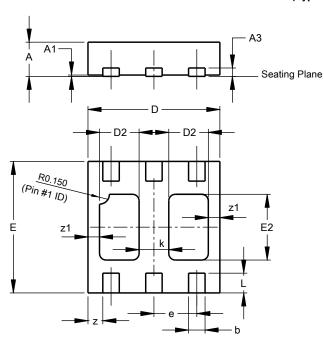
Figure 12 Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type B)

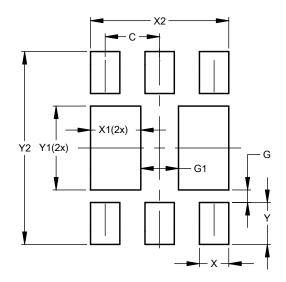


	U-DFN2020-6							
Dim	Type B Dim Min Max Typ							
Α	0.545	0.605	0.575					
A1	0.00	0.05	0.02					
A3	-	-	0.13					
b	0.20	0.30	0.25					
D	1.95	2.075	2.00					
D2	0.50	0.70	0.60					
е	-	-	0.65					
Е	1.95	2.075	2.00					
E2	0.90	1.10	1.00					
k	1	-	0.45					
L	0.25	0.35	0.30					
Z	-	-	0.225					
z1	-	-	0.175					
All	Dimens	ions in	mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type B)



Dimensions	Value		
Dillicitsions	(in mm)		
С	0.650		
G	0.150		
G1	0.450		
X	0.350		
X1	0.600		
X2	1.650		
Υ	0.500		
Y1	1.000		
Y2	2.300		



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